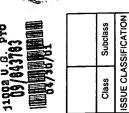
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PATENT DATE

APPLICATION NO.	CONT/PRIOR	CLASS	SUBCLASS	ART UNIT	EXAMINER
09/843783		438	,	2812	O(EMAN)

Basanth Jagannathan Jack Chu Ryan Wuthrich Byeongju Park

Method to increase carbon and boron doping concentrations in Si and SiGe films

ISSUING CLASSIFICATION						
ORIGINAL CROSS REFERENCE(S)						
CLASS	SUBCLASS	ASS CLASS SUBCLASS (ONE SUBCLASS PER BLOCK)				
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TERMINAL	DRAWINGS			CLAIMS ALLOWED		
L DISCLAIMER	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.	
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☐ The term of this patent				NOTICE OF ALL	OWANCE MAILED	
subsequent to (date)						
has been disclaimed.	(Assistant Examiner) (Date)					
The term of this patent shall	Ĭ					
not extend beyond the expiration date of U.S Patent. No				ISS	UE FEE	
				Amount Due	Date Paid	
	(Primary	Examiner)	(Date)			
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this patent have been disclaimed.	(Legal Instrum	ents Examiner)	(Date)			
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